Power LDMOS transistor

Rev. 3 — 1 September 2015



1. Product profile

1.1 General description

A 1200 W LDMOS power transistor for broadcast applications and industrial applications in the HF to 110 MHz band.

Table 1. Application information

Test signal	f	V _{DS}	PL	Gp	η _D
	(MHz)	(V)	(W)	(dB)	(%)
CW	108	50	1000	26	75
pulsed RF	108	50	1200	28.5	75

1.2 Features and benefits

- Typical pulsed performance at frequency of 108 MHz, a supply voltage of 50 V and an I_{Dq} of 40 mA, a t_p of 100 μs with δ of 20 %:
 - ◆ Output power = 1200 W
 - ◆ Power gain = 28.5 dB
 - ◆ Efficiency = 75 %
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (10 MHz to 110 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Industrial, scientific and medical applications
- FM transmitter applications

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2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain1		
2	drain2	1 2	1 . 🔟
3	gate1		3
4	gate2	3 4	5
5	source	[1]	4
			' <u></u>
			2 sym117

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BLF178P	-	flanged balanced LDMOST ceramic package; 2 mounting holes; 4 leads	SOT539A	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	110	V
V_{GS}	gate-source voltage		-0.5	+11	V
I_D	drain current		-	88	Α
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	225	°C

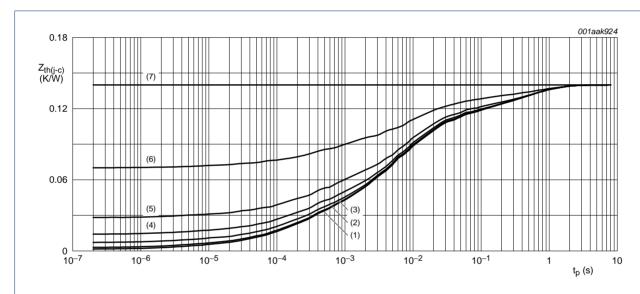
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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _j = 150 °C	[1][2] 0.14	K/W
Z _{th(j-c)}	transient thermal impedance from junction to case	T_j = 150 °C; t_p = 100 μ s; δ = 20 %	[3] 0.04	K/W

- [1] T_i is the junction temperature.
- [2] $R_{th(j-c)}$ is measured under RF conditions.
- [3] See Figure 1.



- (1) $\delta = 1 \%$
- (2) $\delta = 2 \%$
- (3) $\delta = 5 \%$
- (4) δ = 10 %
- (5) $\delta = 20 \%$
- (6) $\delta = 50 \%$
- (7) $\delta = 100 \% (DC)$

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

6. Characteristics

Table 6. DC characteristics

 $T_j = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.5 \text{ mA}$	110	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 500 mA	1.25	1.7	2.25	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 50 V; I_{D} = 20 mA	8.0	1.3	1.8	V
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	-	2.8	μΑ

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Table 6. DC characteristics ... continued

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	58	71	-	Α
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	280	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 16.66 A$	-	0.07	-	Ω
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	-	3	-	pF
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	-	403	-	pF
C _{oss}	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	-	138	-	pF

Table 7. RF characteristics

Test signal: pulsed RF; t_p = 100 μ s; δ = 20 %; f = 108 MHz; RF performance at V_{DS} = 50 V; I_{Dq} = 40 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

7						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L} = 1200 \text{ W}$	27	28.5	31	dB
RLin	input return loss	P _L = 1200 W	-	-16	-12	dB
η_{D}	drain efficiency	P _L = 1200 W	71	75	-	%

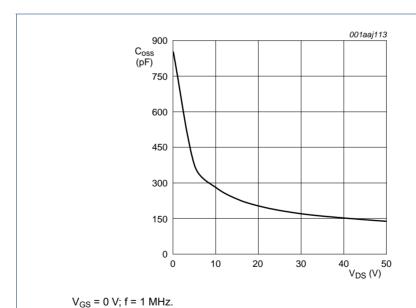


Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

6.1 Ruggedness in class-AB operation

The BLF178P is capable of withstanding a load mismatch corresponding to VSWR = 13 : 1 through all phases under the following conditions: V_{DS} = 50 V; I_{Dq} = 40 mA; P_{L} = 1200 W pulsed; f = 108 MHz.

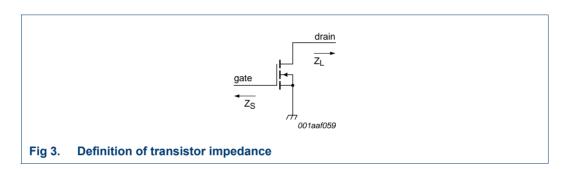
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7. Test information

7.1 Impedance information

Table 8. Typical impedance Simulated Z_S and Z_L test circuit impedances.

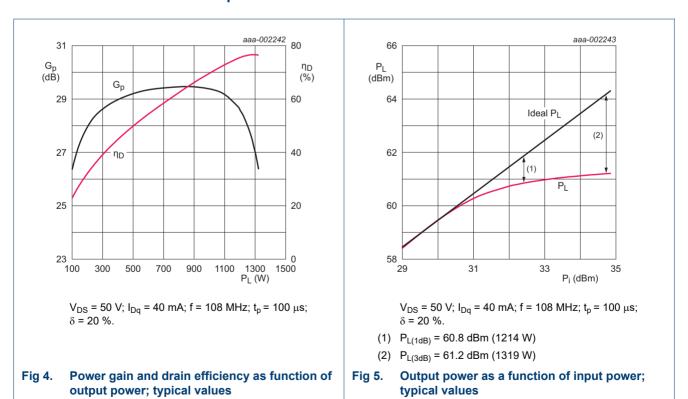
f	Z _S	Z _L
MHz	Ω	Ω
108	3.91 – j3.56	3.59 – j1.73



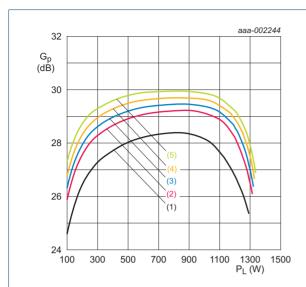
7.2 RF performance

The following figures are measured in a class-AB production test circuit.

7.2.1 1-Tone CW pulsed



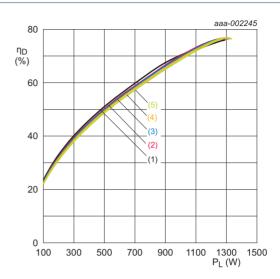
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 V_{DS} = 50 V; f = 108 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $I_{Dq} = 0 \text{ mA}$
- (2) $I_{Dq} = 20 \text{ mA}$
- (3) $I_{Dq} = 40 \text{ mA}$
- (4) $I_{Dq} = 80 \text{ mA}$
- (5) $I_{Dq} = 160 \text{ mA}$

Fig 6. Power gain as a function of output power; typical values



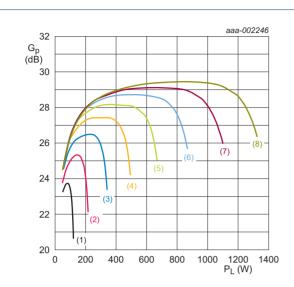
 V_{DS} = 50 V; f = 108 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $I_{Dq} = 0 \text{ mA}$
- (2) $I_{Dq} = 20 \text{ mA}$
- (3) $I_{Dq} = 40 \text{ mA}$
- (4) $I_{Dq} = 80 \text{ mA}$
- (5) $I_{Dq} = 160 \text{ mA}$

Fig 7. Drain efficiency as a function of output power; typical values

6 of 13

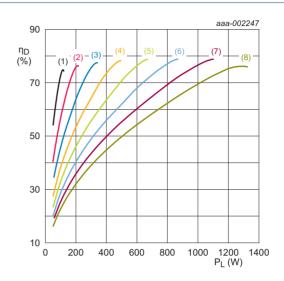
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 I_{Dq} = 40 mA; f = 108 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $V_{DS} = 15 V$
- (2) $V_{DS} = 20 \text{ V}$
- (3) $V_{DS} = 25 \text{ V}$
- (4) $V_{DS} = 30 \text{ V}$
- (5) $V_{DS} = 35 V$
- (6) $V_{DS} = 40 \text{ V}$
- (7) $V_{DS} = 45 \text{ V}$
- (8) $V_{DS} = 50 \text{ V}$

Fig 8. Power gain as a function of output power; typical values



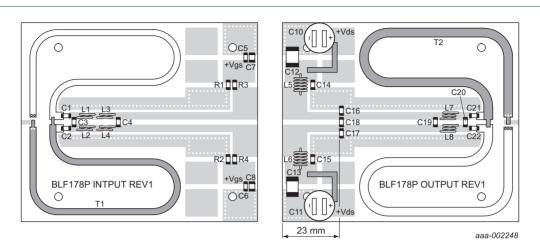
 I_{Dq} = 40 mA; f = 108 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $V_{DS} = 15 V$
- (2) $V_{DS} = 20 \text{ V}$
- (3) $V_{DS} = 25 V$
- (4) $V_{DS} = 30 \text{ V}$
- (5) $V_{DS} = 35 V$
- (6) $V_{DS} = 40 \text{ V}$
- (7) $V_{DS} = 45 V$
- (8) $V_{DS} = 50 \text{ V}$

Fig 9. Drain efficiency as a function of output power; typical values

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7.3 Test circuit



Printed-Circuit Board (PCB): RF 35; ϵ_r = 3.5; thickness = 0.76 mm; thickness copper plating = 35 μ m. See Table 9 for a list of components.

Fig 10. Component layout for class-AB production test circuit

Table 9. List of components For test circuit see Figure 10.

Component	Description	Value	Remarks
C1, C2, C5, C6, C14, C15, C21, C22	multilayer ceramic chip capacitor	1 nF	[1]
C3	multilayer ceramic chip capacitor	82 pF	[1]
C4	multilayer ceramic chip capacitor	240 pF	[1]
C7, C8	multilayer ceramic chip capacitor	4.7 μF; 50 V	
C10, C11	electrolytic capacitor	1000 μF; 63 V	
C12, C13	multilayer ceramic chip capacitor	4.7 μF; 100 V	
C16, C17	multilayer ceramic chip capacitor	120 pF	<u>[1]</u>
C18	multilayer ceramic chip capacitor	82 pF	<u>[1]</u>
C19	multilayer ceramic chip capacitor	110 pF	<u>[1]</u>
C20	multilayer ceramic chip capacitor	56 pF	<u>[1]</u>
L1, L2, L3, L4	1.5 turn 0.8 mm copper wire	D = 3 mm; length = 2 mm	
L5, L6	5 turn 0.8 mm copper wire	D = 3 mm; length = 4.5 mm	
L7, L8	2.5 turn 0.8 mm copper wire	D = 3 mm; length = 3 mm	
R1, R2	SMD resistor	100 Ω	Philips 1206
R3, R4	SMD resistor	9.1 Ω	Philips 1206
T1	semi rigid coax	25 $Ω$; 160 mm	UT-090C-25
T2	semi rigid coax	25 $Ω$; 160 mm	UT-141C-25

^[1] American Technical Ceramics type 800B or capacitor of same quality.

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8. Package outline

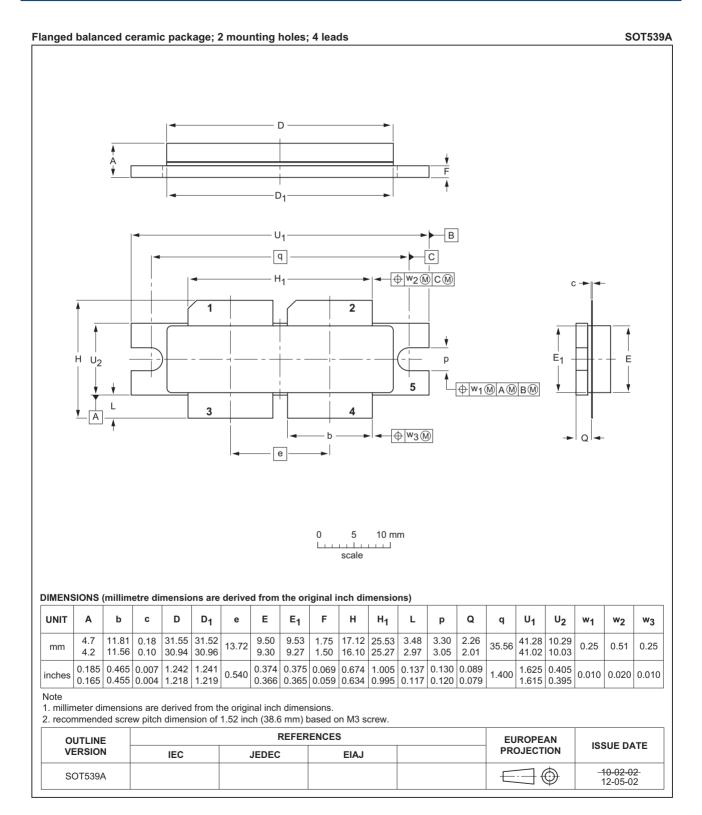


Fig 11. Package outline SOT539A

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9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
CW	Continuous Wave
DC	Direct Current
ESD	ElectroStatic Discharge
FM	Frequency Modulation
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
RF	Radio Frequency
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF178P#3	20150901	Product data sheet	-	BLF178P v.2
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. 			
	 Legal texts ha 	ive been adapted to the new compan	y name where appropriate.	
BLF178P v.2	20120216	Product data sheet	-	BLF178P v.1
BLF178P v.1	20110405	Objective data sheet	-	-

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12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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